

MMBT5088L, MMBT5089L

Low Noise Transistors

NPN Silicon

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage MMBT5088L MMBT5089L	V_{CEO}	30 25	Vdc
Collector–Base Voltage MMBT5088L MMBT5089L	V_{CBO}	35 30	Vdc
Emitter–Base Voltage	V_{EBO}	4.5	Vdc
Collector Current – Continuous	I_C	50	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

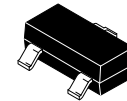
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

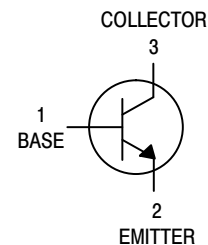


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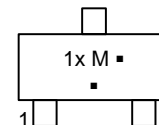
www.onsemi.com



SOT-23 (TO-236)
CASE 318
STYLE 6



MARKING DIAGRAM



- 1x = Device Code
 x = Q for MMBT5088L
 SMMBT5088L
 x = R for MMBT5089L
 SMMBT5089L
 M = Date Code*
 ■ = Pb-Free Package

(Note: Microdot may be in either location)
 *Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT5088LT1G, SMMBT5088LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSVMMBT5088LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBT5089LT1G, SMMBT5089LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT5088L, MMBT5089L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I _C = 1.0 mA, I _B = 0)	MMBT5088L MMBT5089L	V _{(BR)CEO}	30 25	– –	Vdc
Collector–Base Breakdown Voltage (I _C = 100 μA, I _E = 0)	MMBT5088L MMBT5089L	V _{(BR)CBO}	35 30	– –	Vdc
Collector Cutoff Current (V _{CB} = 20 Vdc, I _E = 0) (V _{CB} = 15 Vdc, I _E = 0)	MMBT5088L MMBT5089L	I _{CBO}	– –	50 50	nAdc
Emitter Cutoff Current (V _{EB(off)} = 3.0 Vdc, I _C = 0) (V _{EB(off)} = 4.5 Vdc, I _C = 0)	MMBT5088L MMBT5089L	I _{EBO}	– –	50 100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I _C = 100 μA, V _{CE} = 5.0 Vdc) (I _C = 1.0 mA, V _{CE} = 5.0 Vdc) (I _C = 10 mA, V _{CE} = 5.0 Vdc)	MMBT5088L MMBT5089L MMBT5088L MMBT5089L MMBT5088L MMBT5089L	h _{FE}	300 400 350 450 300 400	900 1200 – – – –	–
Collector–Emitter Saturation Voltage (I _C = 10 mA, I _B = 1.0 mA)		V _{CE(sat)}	–	0.5	Vdc
Base–Emitter Saturation Voltage (I _C = 10 mA, I _B = 1.0 mA)		V _{BE(sat)}	–	0.8	Vdc
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain — Bandwidth Product (I _C = 500 μA, V _{CE} = 5.0 Vdc, f = 20 MHz)		f _T	50	–	MHz
Collector–Base Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz emitter guarded)		C _{cb}	–	4.0	pF
Emitter–Base Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz collector guarded)		C _{eb}	–	10	pF
Small Signal Current Gain (I _C = 1.0 mA, V _{CE} = 5.0 Vdc, f = 1.0 kHz)	MMBT5088L MMBT5089L	h _{fe}	350 450	1400 1800	–
Noise Figure (I _C = 100 μA, V _{CE} = 5.0 Vdc, R _S = 10 kΩ, f = 1.0 kHz)	MMBT5088L MMBT5089L	NF	– –	3.0 2.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

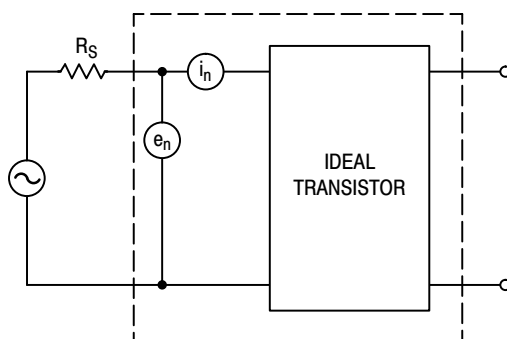


Figure 1. Transistor Noise Model

MMBT5088L, MMBT5089L

NOISE CHARACTERISTICS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

NOISE VOLTAGE

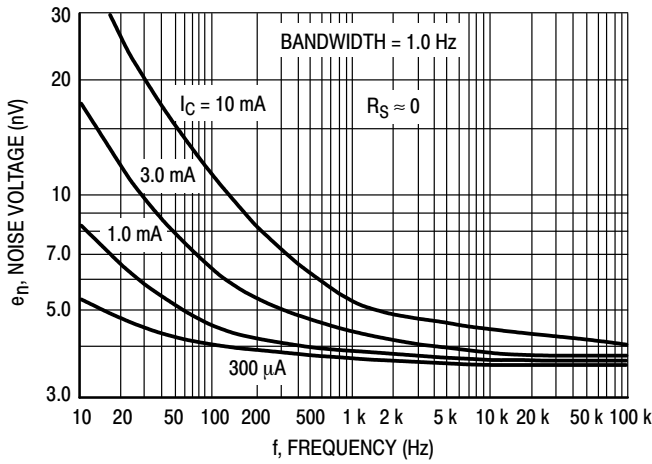


Figure 2. Effects of Frequency

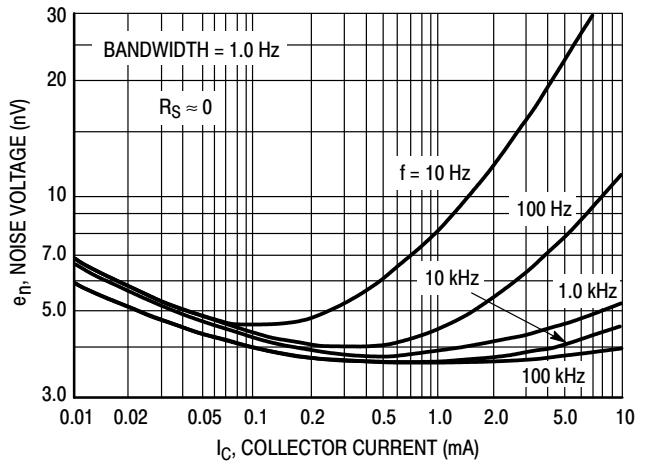


Figure 3. Effects of Collector Current

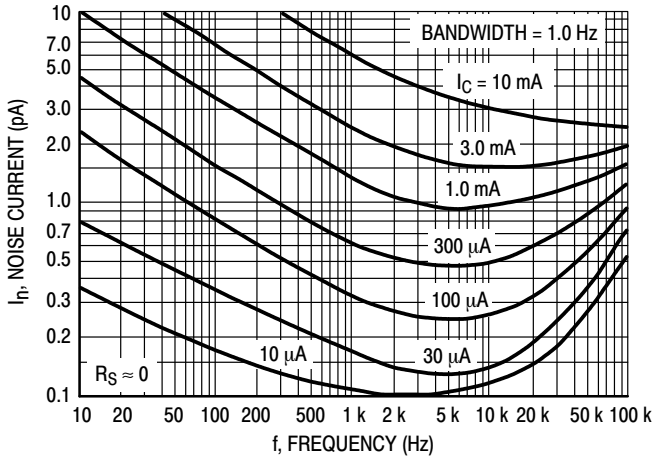


Figure 4. Noise Current

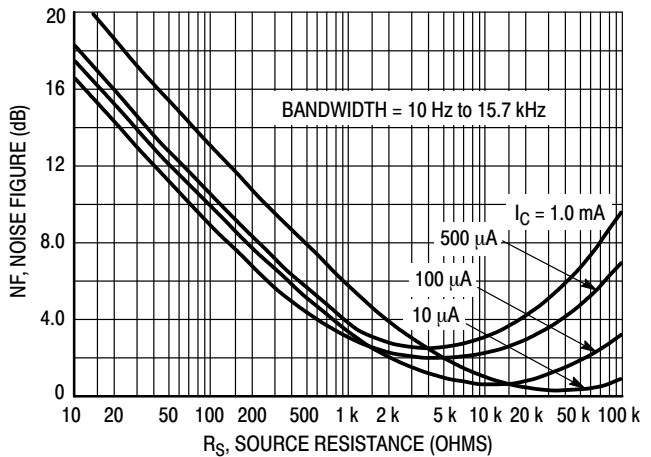


Figure 5. Wideband Noise Figure

100 Hz NOISE DATA

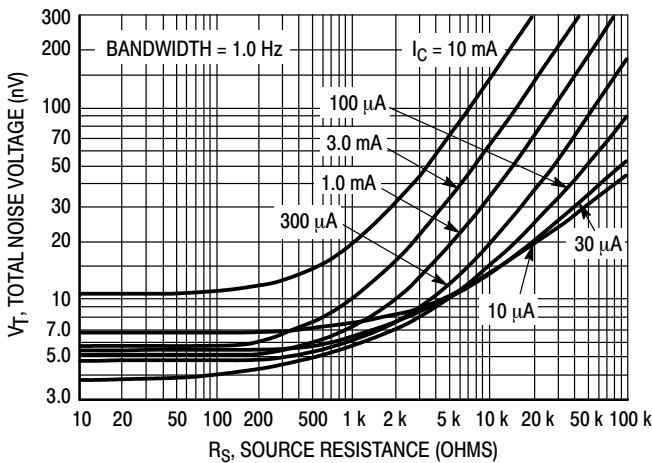


Figure 6. Total Noise Voltage

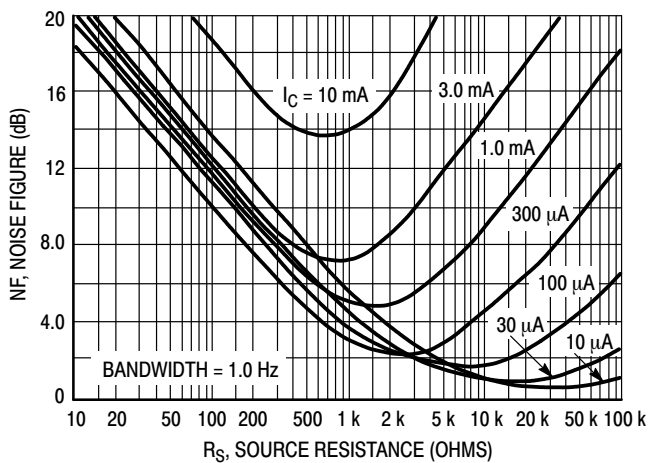


Figure 7. Noise Figure

MMBT5088L, MMBT5089L

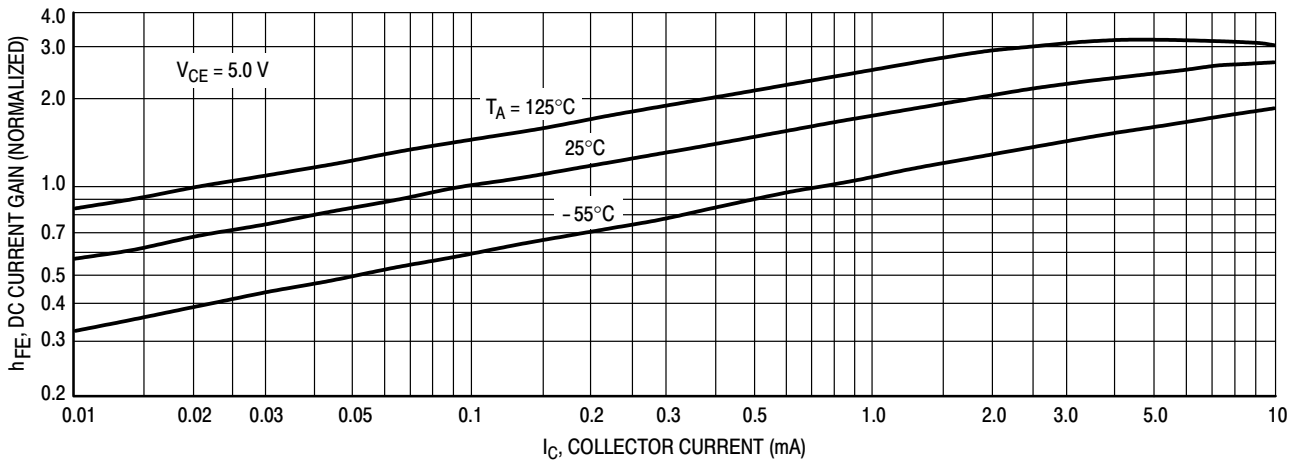


Figure 8. DC Current Gain

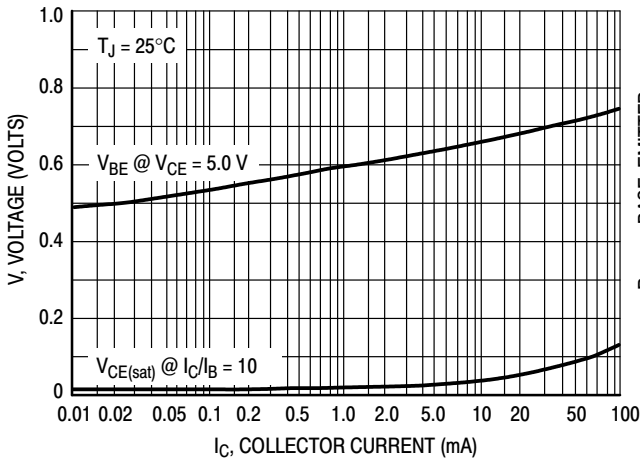


Figure 11. "On" Voltages

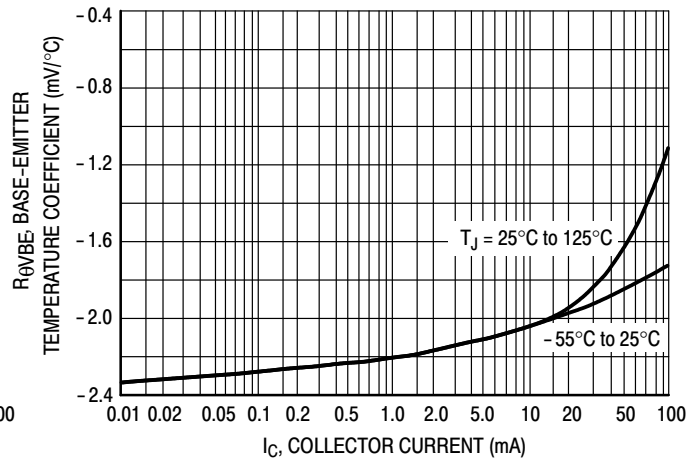


Figure 9. Temperature Coefficients

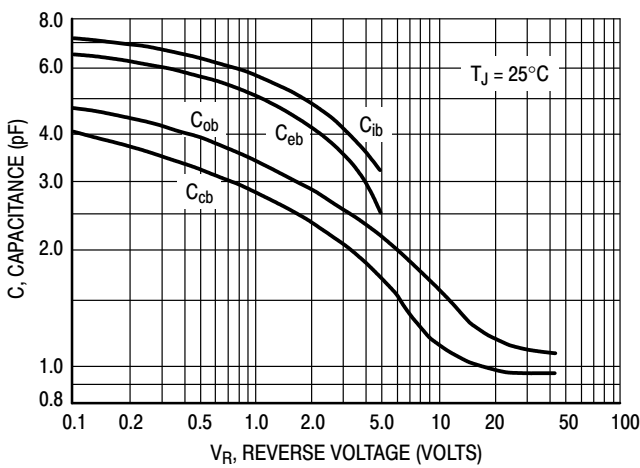


Figure 12. Capacitance

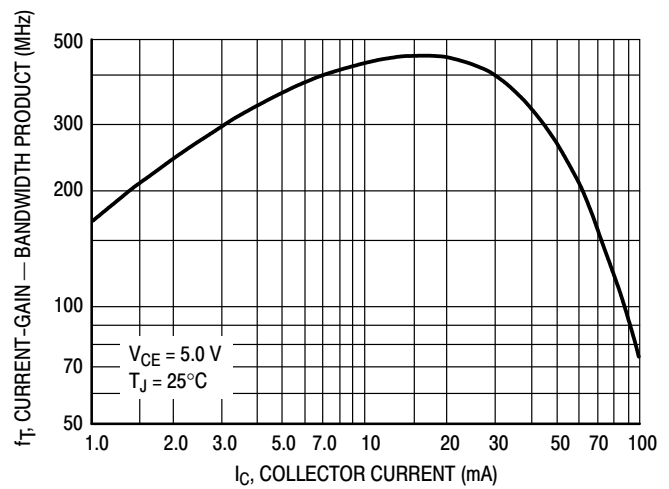


Figure 10. Current-Gain — Bandwidth Product

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SOT-23 (TO-236)
CASE 318-08
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1

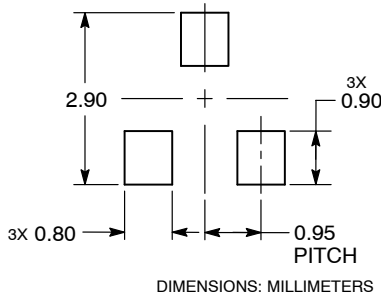


NOTES:

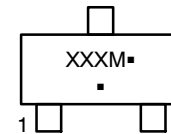
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

RECOMMENDED SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- | | | | |
|---|---|---|--|
| STYLE 1 THRU 5:
CANCELLED | STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR | STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE |
| STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE | STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE | STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE |
| STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE | STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE | STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE | STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE |
| STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE | STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE | STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE | STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE |
| STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN | STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT | STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE |
| STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE | STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION | STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE | STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE |

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